Micron announces first high-volume Phase Change Memory modules for mobile devices

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Micron Technology, one of the world's leading providers of advanced semiconductor solutions, today announced an industry first with high-volume availability of its 45-nanometer (nm) Phase Change Memory (PCM) for mobile devices, featuring 1-gigabit (Gb) PCM plus 512-megabit (Mb) LPDDR2 in a multichip package.

As the first company in the world currently offering PCM solutions in volume production, Micron is providing chipset vendors, enablers, and handset manufacturers with a proven product that meets the expanding needs of today's wireless market and paves the way for enhanced features and capabilities.

PCM provides enhanced boot time, simplifies software development and boosts performance with overwrite capability. It also provides very low power consumption and extremely high reliability. In addition, the design-optimizing shared interface between LPDDR2 and PCM is fully compliant with JEDEC industry standards.

Micron's 45nm PCM solution is currently targeted for utilization in feature phones, with a future roadmap aimed at addressing smartphones and media tablets.

Micron's PCM product line has established a foothold in the wireless industry, as evidenced by longstanding key relationships with global customers and enablers, ongoing engagement with major device manufactures, and strong cooperation with Intel Mobile

Communications, which includes recent PCM qualification.

From entry-level phones to high-end smartphones and tablets, Micron supplies virtually every volatile and nonvolatile memory product utilized in wireless devices today, including NOR, NAND, PCM, LPDRAM and e·MMC embedded memory, meeting the need for increased performance, expanding storage requirements, mature technology replacement, and package capability.

Source: Micron Technology

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